

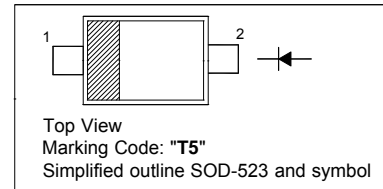
## 1N4448WT

### Silicon Epitaxial Planar Switching Diode

Fast Switching Diode

#### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



#### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	$V_{RM}$	100	V
Reverse Voltage	$V_R$	80	V
Average Rectified Forward Current	$I_{F(AV)}$	125	mA
Forward Continuous Current	$I_{FM}$	250	mA
Non-Repetitive Peak Forward Surge Current (at $t = 1\text{ }\mu\text{s}$ )	$I_{FSM}$	0.5	A
Power Dissipation	$P_d$	150	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 65 to + 150	$^\circ\text{C}$

#### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 5\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 100\text{ mA}$ at $I_F = 150\text{ mA}$	$V_F$	0.62 - - -	0.72 0.855 1 1.25	V
Reverse Leakage Current at $V_R = 80\text{ V}$ at $V_R = 20\text{ V}$ at $V_R = 75\text{ V}$ , $T_J = 150\text{ }^\circ\text{C}$ at $V_R = 25\text{ V}$ , $T_J = 150\text{ }^\circ\text{C}$	$I_R$	- - - -	100 25 50 30	nA nA $\mu\text{A}$ $\mu\text{A}$
Reverse Breakdown Voltage at $I_R = 100\text{ }\mu\text{A}$	$V_{(BR)R}$	80	-	V
Capacitance at $V_R = 0.5\text{ V}$ , $f = 1\text{ MHz}$	$C_{tot}$	-	4	pF
Reverse Recovery Time at $I_F = I_R = 10\text{ mA}$ , $I_{rr} = 0.1 \times I_R$ , $R_L = 100\text{ }\Omega$	$t_{rr}$	-	4	ns

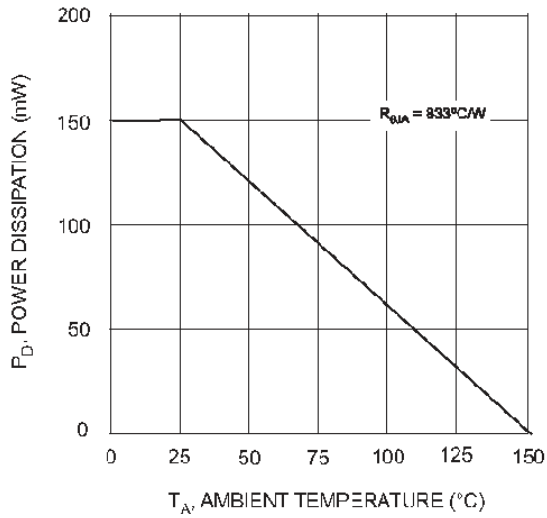


Fig. 1 Derating Curve

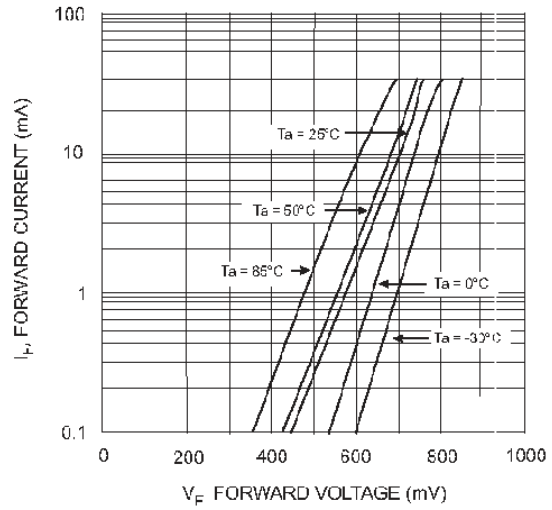


Fig. 2 Typical Forward Characteristics

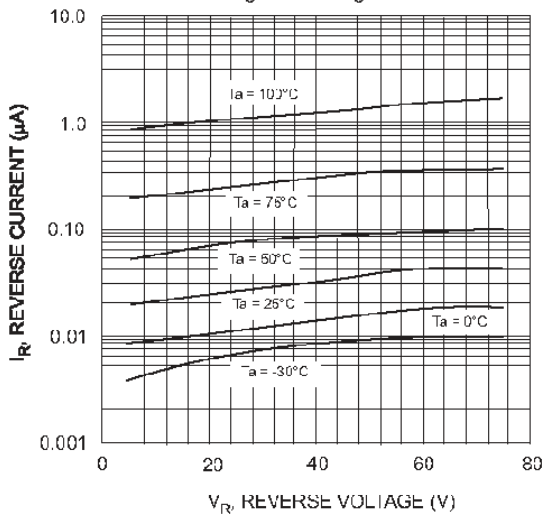


Fig. 3 Typical Reverse Characteristics

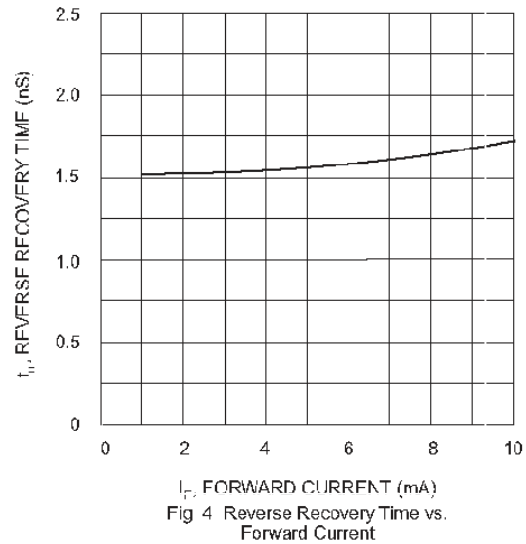
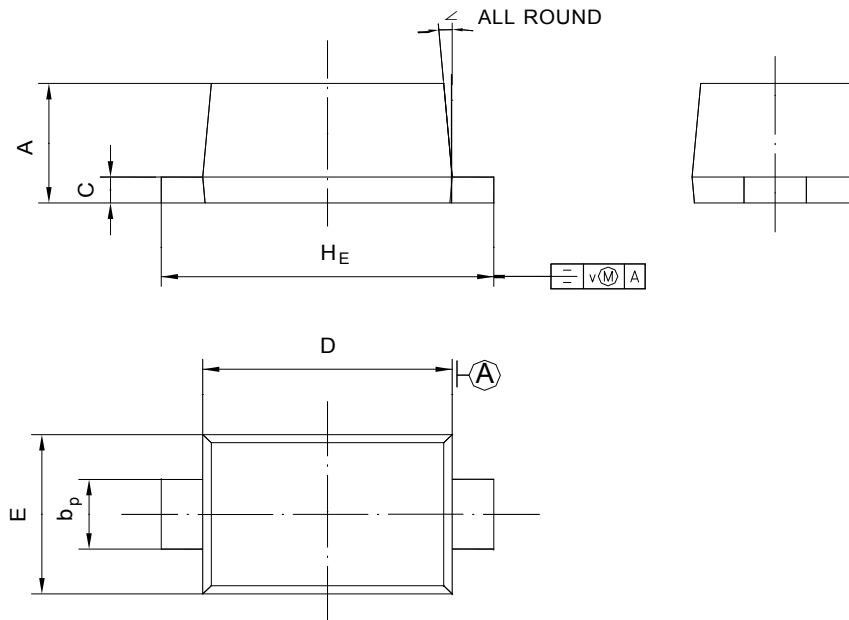


Fig. 4 Reverse Recovery Time vs. Forward Current

## PACKAGE OUTLINE

SOD-523

Plastic surface mounted package; 2 leads



UNIT	A	b <sub>p</sub>	C	D	E	H <sub>E</sub>	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°